

IN THE CLAIMS

Please cancel claims 7-33 without prejudice.

Please amend the following claims. Please add new claims 34-39.

1. (Previously Amended) A method of rinsing a wafer comprising:
spinning a wafer;
exposing said spinning wafer to DI water while providing sonic waves
to substantially the entire surface area of the wafer; and
after exposing said spinning wafer to DI water, exposing said spinning
wafer to a liquid or vapor having a lower surface tension than water.
2. (Previously Amended) The method of claim 1 wherein said liquid is or
vapor comprises isopropyl alcohol (IPA).
3. (Previously Amended) The method of claim 1 wherein said sonic
waves are applied to the backside of said wafer.
4. (Original) The method of claim 1 further comprising the step of
heating said DI water to a temperature greater than room temperature prior to
exposing said spinning wafer to said DI water.
5. (Previously Amended) The method of claim 1 wherein said wafer is
spun at a rate between 50-1000 rpms while exposing said wafer to said DI water and
to said liquid or vapor.

6. (Previously Amended) The method of claim 2 wherein the time of exposure to said liquid is less than time of exposure to said DI water or vapor.

7-33. (Canceled)

34. (New) A method of rinsing a wafer comprising:
spinning a wafer;
exposing said spinning wafer to water while providing sonic waves to substantially the entire surface area of the wafer; and
after exposing said spinning wafer to water, exposing said spinning wafer to a liquid or vapor having a lower surface tension than water.

35. (New) The method of claim 34 wherein said liquid is or vapor comprises isopropyl alcohol (IPA).

36. (New) The method of claim 34 wherein said sonic waves are applied to the backside of said wafer.

37. (New) The method of claim 34 further comprising the step of heating said DI water to a temperature greater than room temperature prior to exposing said spinning wafer to said water.

38. (New) The method of claim 34 wherein said wafer is spun at a rate between 50-1000 rpms while exposing said wafer to said water and to said liquid or vapor.

39. (New) The method of claim 35 wherein the time of exposure to said liquid is less than time of exposure to said water or vapor.